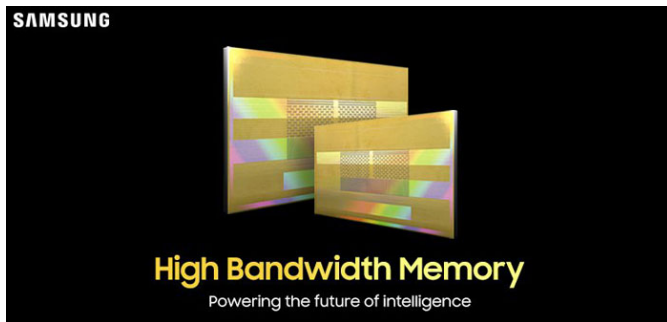


Samsung Produces HBM2E Memory

Written by Frederick Douglas
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Samsung takes to the Nvidia GPU Technology Conference (GTC) to present a High Bandwidth Memory (HBM2E) product-- Flashbolt a high-performance DRAM claiming data transfers reaching up to 3.2Gbps per pin.



Initially aimed for use in next-gen supercomputers, graphics systems and AI, HBM2E offers a 33% increase in speed over the previous generation HBM2, with a density of 16Gb per die (or double the capacity of the previous generation). Such improvements, Samsung says, allow a single HBM2E package to provide 410GBps data bandwidth and 16GB of memory.

“Flashbolt’s industry-leading performance will enable enhanced solutions for next-generation data centers, artificial intelligence, machine learning, and graphics applications,” the company says. “We will continue to expand our premium DRAM offering, and improve our ‘high-performance, high capacity, and low power’ memory segment to meet market demand.”

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